

Silicon NPN Power Transistors

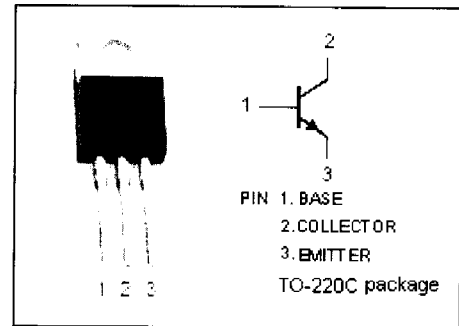
MJE13070/13071

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V(\text{Min})$ - MJE13070
= $450V(\text{Min})$ - MJE13071
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 3.0V(\text{Min})@I_C = 5A$

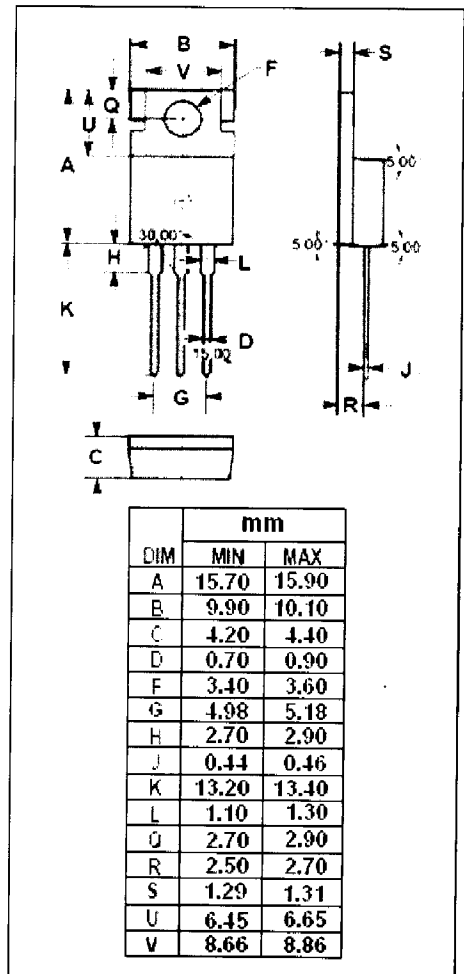
APPLICATIONS

- Designed for high-voltage, high-speed, power switching in inductive circuits, where fall time is critical. They are particularly suited for line-operated switchmode applications such as switching regulators, inverters, DC-DC converter, motor controls, solenoid drive and deflection circuits.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	MJE13070	650
		MJE13071	750
V_{CEO}	Collector-Emitter Voltage	MJE13070	400
		MJE13071	450
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C/W}$

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



Silicon NPN Power Transistors

MJE13070/13071

ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	MJE13070	$I_C = 0.1\text{A}; I_B = 0$	400		V
		MJE13071		450		
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C = 3\text{A}; I_B = 0.6\text{A}$ $I_C = 3\text{A}; I_B = 0.6\text{A}; T_C = 100^\circ\text{C}$		1.0 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C = 5\text{A}; I_B = 1\text{A}$		3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C = 3\text{A}; I_B = 0.6\text{A}$ $I_C = 3\text{A}; I_B = 0.6\text{A}; T_C = 100^\circ\text{C}$		1.5 1.5	V
I_{CEV}	Collector Cutoff Current		$V_{CEV} = \text{Rated Value}; V_{BE(off)} = 1.5\text{V}$ $V_{CEV} = \text{Rated Value}; V_{BE(off)} = 1.5\text{V}; T_C = 100^\circ\text{C}$		0.5 2.5	mA
I_{EBO}	Emitter Cutoff Current		$V_{EB} = 6\text{V}; I_C = 0$		1.0	mA
h_{FE}	DC Current Gain		$I_C = 3\text{A}; V_{CE} = 5\text{V}$	8		
C_{OB}	Output Capacitance		$I_E = 0; V_{CB} = 10\text{V}; f_{test} = 1.0\text{kHz}$		250	pF

Switching Times

t_d	Delay Time	$I_C = 3\text{A}; I_{B1} = 0.4\text{A}; V_{BE(off)} = 5\text{V};$ $V_{CC} = 250\text{V}; t_p = 30\ \mu\text{s}; \text{Duty Cycle} \leq 1\%$		0.05	μs
t_r	Rise Time			0.4	μs
t_{stg}	Storage Time			1.5	μs
t_f	Fall Time			0.5	μs